Leiditech

LM605ESDP5-0.36

- 4-Channel Uni-directional ESD diode

芯片图 WAFER DIAGRAM

产品印记 MARKING

PIN1

1.0 材料规格 MATERIAL

芯片型号 (Die Type)	LM605ESDP5-0.36	Top metal for wire bond	4μm AlSiCu
		Gross die per wafer	120,000 dies
		芯片尺寸 (Die Size)	360×360μm
		晶圆厚度 (Wafer Thickness)	150±10μm
焊区厚度（Weld Thickness）		焊区尺寸（Weld Size）	75×75μm
焊接方式 (Die Attach Type)		切割道 (Scribe Line)	50μm
框架型号 (Lead Frame)		芯片厚度 (Wafer thickness)	152±8μm
焊线规格 (Wire Size)		晶圆直径 (Wafer Diameter)	6 inch
电镀方式 (Plating Method)	---	芯 片 背 材 (BackMetal Material)	TiNiAg

测试规范

Electrical Characteristics (TA=25℃ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	7.0	8.0	9.5	V	I_T=1mA
Leakage Current	I_{Leak}			100	nA	V_{RWM}=5V
正向电压	VF			1.1	V	IF=10mA

NOTICE
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